

isc Silicon PNP Darlington Power Transistor

BD896

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= -45V(Min)
- · High DC Current Gain
- : h_{FE}= 750(Min) @I_C= -3A
- · Collector Power Dissipation-
- : P_C= 70W@ T_C= 25°C
- 8 A Continuous Collector Current
- Complement to Type BD895
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



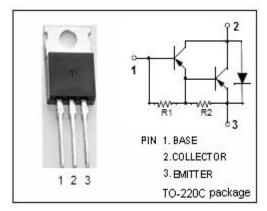
 Designed for use as complementary AF push-pull output stage applications

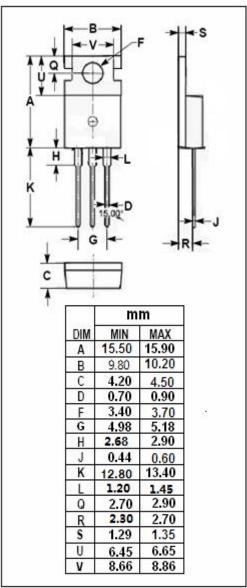
ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|--|-----------|---------------|--|
| V _{CBO} | Collector-Base Voltage | Itage -45 | | |
| V _{CEO} | Collector-Emitter Voltage | -45 | V | |
| V _{EBO} | Emitter-Base Voltage | -5 | V | |
| Ic | Collector Current-Continuous | -8 | Α | |
| I _B | Base Current-Continuous | -0.3 | Α | |
| Pc | Collector Power Dissipation @ T _a =25°C | 2 | 10/ | |
| | Collector Power Dissipation @ T _C =25℃ | 70 | W | |
| TJ | Junction Temperature 150 | | $^{\circ}$ | |
| T _{stg} | Storage Temperature Range | -65~150 | ${\mathbb C}$ | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|---|------|------|
| R _{th j-c} | Thermal Resistance,Junction to Case | 1.79 | °C/W |
| R _{th j-a} | Thermal Resistance, Junction to Ambient | 62.5 | °C/W |







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = -50mA; I _B = 0 | -45 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -3A; I _B = -12mA | | | -2.5 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = -3A ; V _{CE} = -3V | | | -2.5 | V |
| І _{сво} | Collector Cutoff Current | V _{CB} = -45V; I _E = 0 | | | -0.2 | - mA |
| | | V _{CB} = -45V; I _E = 0; T _C = 100 °C | | | -2.0 | IIIA |
| I _{CEO} | Collector Cutoff Current | V _{CE} = -30V; I _B = 0 | | | -0.5 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -5V; I _C = 0 | | | -2 | mA |
| h _{FE} | DC Current Gain | I _C = -3A ; V _{CE} = -3V | 750 | | | |



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